AMENDMENTS TO THE SPECIFICATION

Please amend the following paragraphs as noted:

--[0023] The strained layer 2 is advantageously formed on the donor substrate 1 by crystal growth, such as by epitaxial growth, using known techniques such as, for example, LPD, Chemical Vapor Deposition (CVD) and Molecular Beam Epitaxy (MBE). It is advantageous to choose crystalline materials made of the donor substrate 1 and the strained layer 2 (in the vicinity of its interface with the carrier substrate 1) so that a sufficiently small difference exists between the first and the second respective nominal mesh parameters to obtain a strained layer 2 without too many crystallographic defects. Such a technique avoids, for example, point defects or extensive defects such as dislocations. The difference in mesh parameter is typically between about 0.5% and about 1.5%, but can also have more significant values. For example, $Si_{1-x}Ge_x$ with $x = 0.3$ has a nominal mesh parameter about 1.15% higher than that of Si. But it is preferable for the strained layer 2 to be of approximately constant thickness, so that it presents approximately constant intrinsic properties and/or to facilitate the future bonding with the receiver substrate ~~[[5]]~~ 7 (as shown in FIG. 1e).--.

--[0026] FIG. 1c illustrates a vitreous layer 4 formed on the strained layer 2, and the vitreous layer could also be formed on the receiver substrate 7, which is shown in Figures 1e through 1h. The material of the vitreous layer 4 becomes viscous above a viscosity temperature T_G. In the framework of the present method, a material is chosen for the vitreous layer 4 which has a minimum high viscosity temperature T_G of about 900°C. This high viscosity temperature makes it possible to conduct high temperature thermal treatments without causing the vitreous layer 4 to become viscous. Thus, with reference to FIGS. 1h and 1i, the structures 30 or 40 resulting from performing the present method will not have a part of their crystallographic structure modified by a viscous vitreous layer 4. A single thermal treatment at a temperature around or above T_G will however be applied during the process (with reference to FIG. 1h) to relax the strained layer 2 to form a relaxed layer 2'. It is particularly advantageous to be able to retain the at least relative relaxation strength (which is obtained during a step with reference to

FIG. 1h) of the $Si_{1-x}Ge_x$ layer up to a temperature of somewhere around 900°C. or even at a higher temperature.--

--[0062] With reference to FIGs. 2h and 2i, the inserted strained layer 5' is retained after the thermal treatment to relax the strained layer 2. The structure 30 that is formed includes a relaxed $Si_{1-x}Ge_x$ layer 2', a strained Si layer 5', a vitreous layer 4, and a receiver substrate 7. This structure 30 is a SG/SOI structure, where the vitreous layer 4 is electrically insulating, such as for example a vitreous layer 4 of SiO_2. --.